

DATASHEET

# UJ3D06512TS

## 12A - 650V SiC Schottky Diode

Rev. A, June 2019

### Description

United Silicon Carbide, Inc. offers the 3<sup>rd</sup> generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.

### Features

- ◆ Maximum operating temperature of 175°C
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified

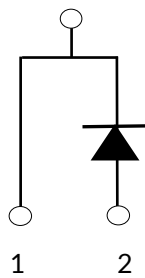
### Typical applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switch mode power supplies
- ◆ Power factor correction modules

CASE



CASE



Part Number	Package	Marking
UJ3D06512TS	TO-220-2L	UJ3D06512TS



## Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	$V_R$		650	V
Repetitive peak reverse voltage, $T_J=25^\circ\text{C}$	$V_{RRM}$		650	V
Surge peak reverse voltage	$V_{RSM}$		650	V
Maximum DC forward current	$I_F$	$T_C = 153^\circ\text{C}$	12	A
Non-repetitive forward surge current sine halfwave	$I_{FSM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	81	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	70	
Repetitive forward surge current sine halfwave, $D=0.1$	$I_{FRM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	53	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	32.5	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	480	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	480	
$i^2t$ value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	32.8	$\text{A}^2\text{s}$
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	24.5	
Power dissipation	$P_{tot}$	$T_C = 25^\circ\text{C}$	187.5	W
		$T_C = 153^\circ\text{C}$	27.5	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	$T_J, T_{STG}$		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	$T_{sold}$	1.6mm from case for 10s	260	$^\circ\text{C}$

## Thermal Characteristics

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction-to-case	$R_{\theta JC}$			0.6	0.8	$^\circ\text{C}/\text{W}$

## Electrical Characteristics ( $T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	$V_F$	$I_F = 12\text{A}, T_J = 25^\circ\text{C}$	-	1.5	1.7	V
		$I_F = 12\text{A}, T_J = 150^\circ\text{C}$	-	1.8	2.1	
		$I_F = 12\text{A}, T_J = 175^\circ\text{C}$	-	1.9	2.25	
Reverse current	$I_R$	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$	-	1.4	80	$\mu\text{A}$
		$V_R = 650\text{V}, T_J = 175^\circ\text{C}$	-	12		
Total capacitive charge <sup>(1)</sup>	$Q_C$	$V_R = 400\text{V}$		29		nC
Total capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$		392		pF
		$V_R = 300\text{V}, f = 1\text{MHz}$		48		
		$V_R = 600\text{V}, f = 1\text{MHz}$		42		
Capacitance stored energy	$E_C$	$V_R = 400\text{V}$		4.4		$\mu\text{J}$

(1)  $Q_C$  is independent on  $T_J$ ,  $di_F/dt$ , and  $I_F$  as shown in the application note USCi\_AN0011.

## Typical Performance Diagrams

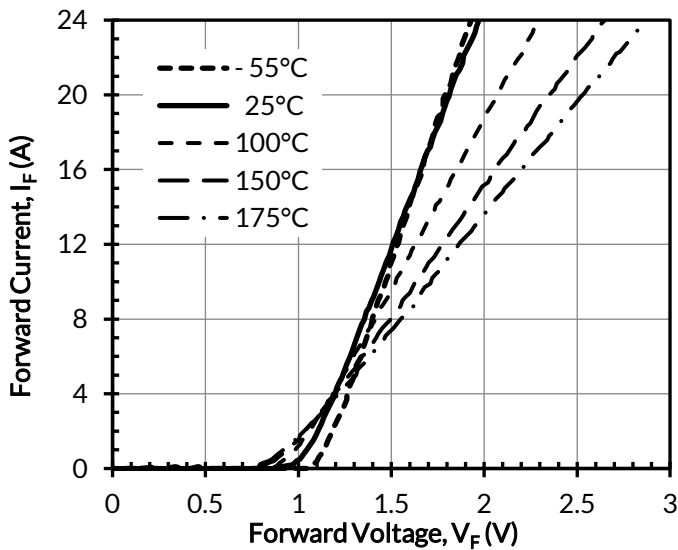


Figure 1. Typical forward characteristics

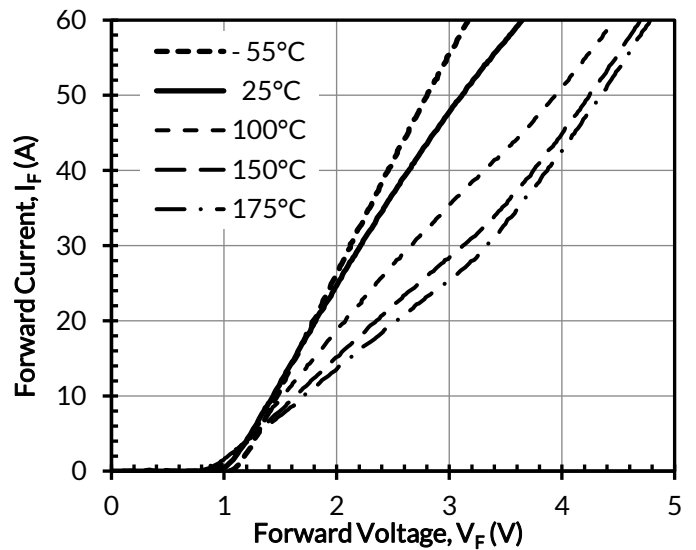


Figure 2. Typical forward characteristics in surge current

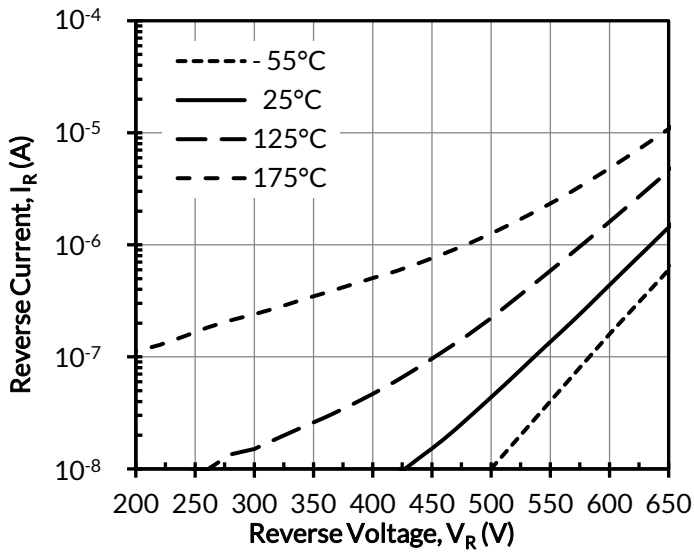


Figure 3. Typical reverse characteristics

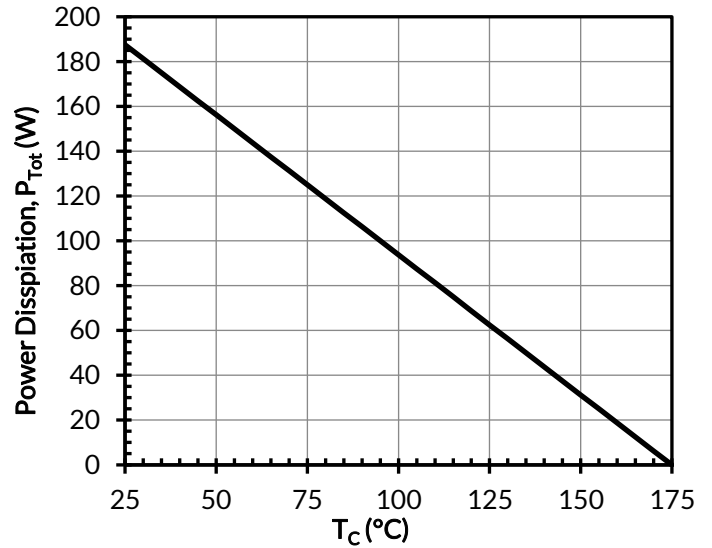


Figure 4. Power dissipation

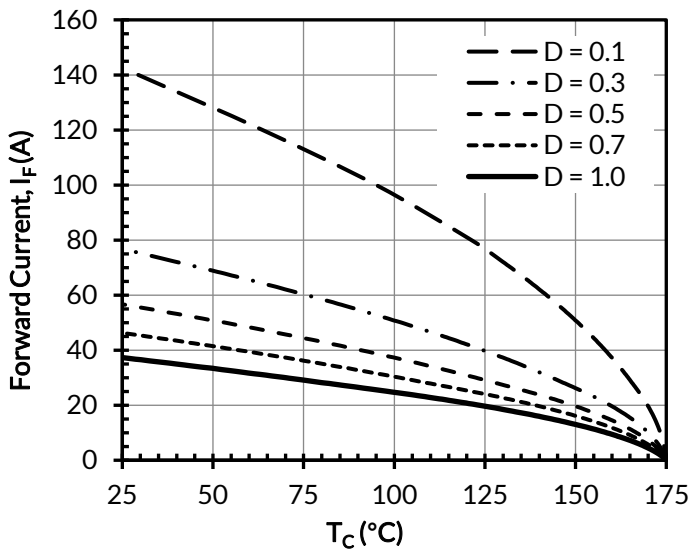


Figure 5. Diode forward current

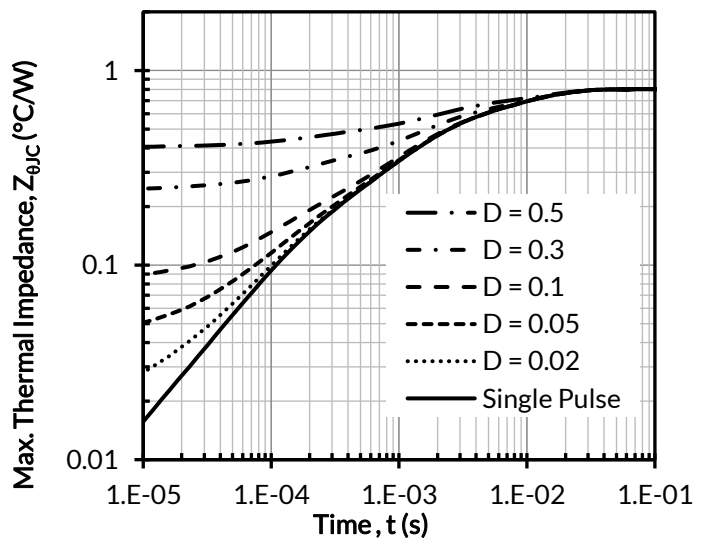


Figure 6. Maximum transient thermal impedance

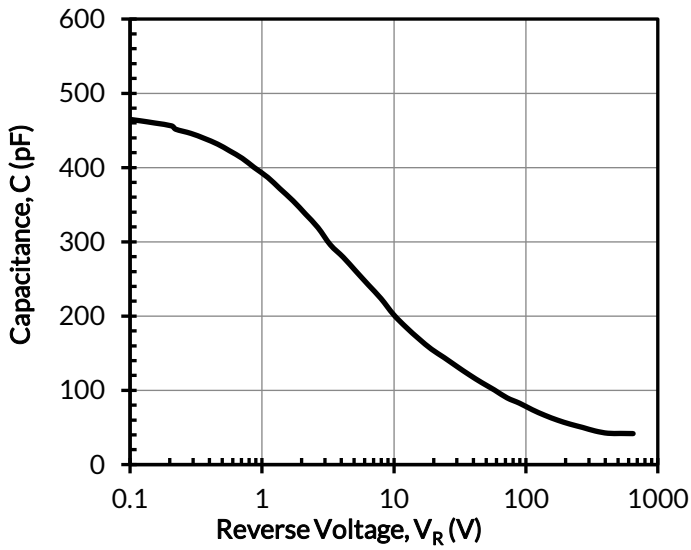


Figure 7. Capacitance vs. reverse voltage at 1MHz

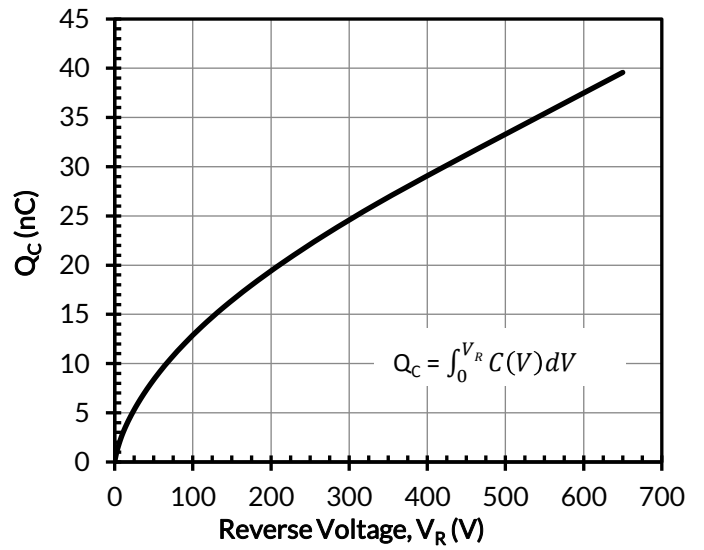


Figure 8. Typical capacitive charge vs. reverse voltage

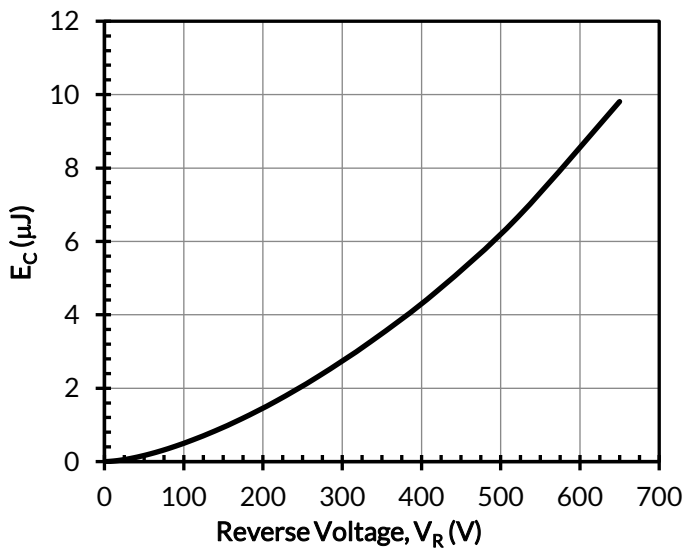


Figure 9. Typical capacitance stored energy vs. reverse voltage